

Silicon Standard Recovery Diode

$V_{RRM} = 50\text{ V} - 600\text{ V}$
 $I_F = 60\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

DO-5 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N2133A (R)	1N2135A (R)	1N2137A (R)	1N2138A (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		300	400	500	600	V
RMS reverse voltage	V_{RMS}		210	280	350	420	V
DC blocking voltage	V_{DC}		50	100	150	200	V
Continuous forward current	I_F	$T_C \leq 150\text{ °C}$	60	60	60	60	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	1050	1050	1050	1050	A
Operating temperature	T_j		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C
Storage temperature	T_{stg}		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	1N2133A (R)	1N2135A (R)	1N2137A (R)	1N2138A (R)	Unit
Diode forward voltage	V_F	$I_F = 60\text{ A}$, $T_j = 25\text{ °C}$	1.1	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ °C}$	10	10	10	10	μA
		$V_R = 50\text{ V}$, $T_j = 150\text{ °C}$	15	15	15	15	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		0.65	0.65	0.65	0.65	°C/W
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